### Zibo Seno Electronic Engineering Co., Ltd.



## MBR540G-MBR52000





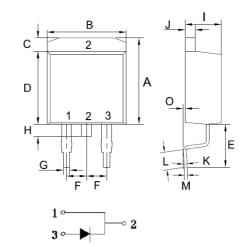
#### **5.0 A SCHOTTKY BARRIER DIODE**

- Schottky Barrier Chip
- Ideally Suited for Automatic Assembly
- Low Power Loss, High Efficiency
- For Use in Low Voltage Application
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-O

#### **Mechanical Data**

- Case: TO-263/D<sup>2</sup>PAK, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: See DiagramMounting Position: Any
- Lead Free: For RoHS / Lead Free Version

## TO-263/D<sup>2</sup>PAK



$TO-263 (D^2 PAK)$										
Unit:mm										
DIM	MIN	MAX								
A	10.44	10.84								
В	9.81	10.21								
С	1.44	1.84								
D	8.80	9.20								
Е	4.46	4.66								
F	2.44	2.64								
G	0.61	1.01								
Н	0.70	1.30								
I	4. 27	4.87								
J	1.07	1.47								
K	0°	8°								
L	2. 10	2.50								
M	0.30	0.46								
0	0	0. 25								

#### Maximum Ratings and Electrical Characteristics @T<sub>A</sub>=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 540G	MBR 545G	MBR 550G	MBR 560G	MBR 580G	MBR 5100G	MBR 5150G	MBR 5200G	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	40	45	50	60	80	100	150	200	V
RMS Reverse Voltage	VR(RMS)	28	31	35	42	56	70	105	140	V
Average Rectified Output Current @T <sub>L</sub> = 75°C (Note 1)	lo	5.0							А	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	100							А	
Forward Voltage @I <sub>F</sub> = 5A	Vғм	0.55 0.70 0.85 0.92				92	V			
	lкм	0.1 20							mA	
Typical Junction Capacitance (Note 2)	Cj	350 280 200				pF				
Typical Thermal Resistance (Note 1)	$R_{ heta}JA$	15						°C/W		
Operating and Storage Temperature Range	Тj, Tsтg	-55 to +125 -55 to +150						°C		

Note: 1. Valid provided that leads are kept at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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# MBR540G-MBR5200G



### **RATING AND CHARACTERISTIC CURVES**

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

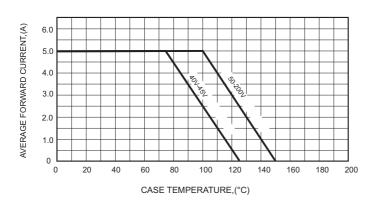


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

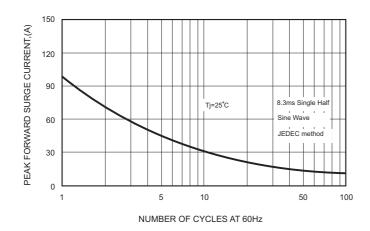


FIG.2-TYPICAL FORWARD

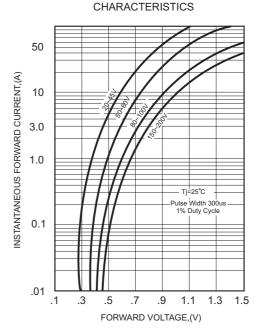


FIG.4 - TYPICAL REVERSE

